

# ROHM AG185FGD3HRB

Nch 40V 80A Power MOSFET

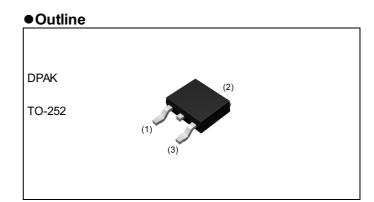
V <sub>DSS</sub>	40V
R <sub>DS(on)</sub> (Max.)	3.2mΩ
Ι <sub>D</sub>	±80A
P <sub>D</sub>	96W

### Features

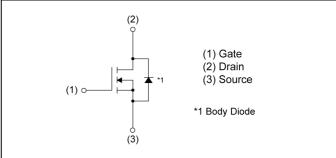
Application

Automotive Systems

Low on-resistance Pb-free plating;RoHS compliant 100% Avalanche tested AEC-Q101 qualified



#### Inner circuit



## Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	16
	Quantity (pcs)	2500
	Taping code	TL
	Marking	AG185FGD3

## • Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V <sub>DSS</sub>	40	V
Continuous drain current	V <sub>GS</sub> = 10V	۱ <sub>D</sub> *1	±80	А
Pulsed drain current		<sup>*2</sup>	±160	А
Gate - Source voltage		V <sub>GSS</sub>	±20	V
Avalanche current, single pulse		I <sub>AS</sub> *3	40	А
Avalanche energy, single pulse		$E_{AS}^{*3}$	59	mJ
Power dissipation		P <sub>D</sub> <sup>*1</sup>	96	W
Junction temperature	Т <sub>ј</sub>	175	°C	
Operating junction and storage tem	perature range	T <sub>stg</sub>	-55 to +175	°C

## •Thermal resistance

Parameter	Symbol	Values			Unit
Falameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}^{*1}$	-	-	1.55	°C/W

## •Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	Currence of	Conditions		Values		- Unit	
Parameter	Symbol Conditions –		Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	40	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I <sub>D</sub> = 1mA referenced to 25°C	-	21	-	mV/°C	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V	-	-	1	μA	
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	-	-	±500	nA	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 924 \mu A$	2.0	-	4.0	V	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 924 \mu A$ referenced to 25°C	-	-6.8	-	mV/°C	
Static drain - source	D *4	V <sub>GS</sub> = 10V, I <sub>D</sub> = 80A	-	2.5	3.2		
on - state resistance	R <sub>DS(on)</sub> *4	V <sub>GS</sub> = 6V, I <sub>D</sub> = 40A	-	3.3	4.6	mΩ	
Gate resistance	R <sub>G</sub>	f = 1MHz, open drain	-	3.1	-	Ω	
Forward Transfer Admittance	Y <sub>fs</sub>   <sup>*4</sup>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A	14	-	-	S	

\*1 T<sub>c</sub>=25°C , Limited only by maximum junction temperature Tj=175°C.

\*2 Pw  ${\leq}10\mu s$  , Duty cycle  ${\leq}1\%$ 

\*3 L=0.05mH, V<sub>DD</sub>=20V, R<sub>G</sub>=25 $\Omega$ , Starting Tj=25°C, See Fig.3-1,3-2

\*4 Pulsed



# •Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	Symbol		Values			Unit	
Parameter	Symbol	ol Conditions –		Тур.	Max.	UTIIL	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2800	-		
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V	-	1180	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	90	-		
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq 20V, V_{GS}$ = 10V	-	32	-		
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = 10A	-	17	-		
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L \simeq 2\Omega$	-	65	-	ns	
Fall time	t <sub>f</sub> *4	R <sub>G</sub> = 1Ω	-	14	-		

# • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

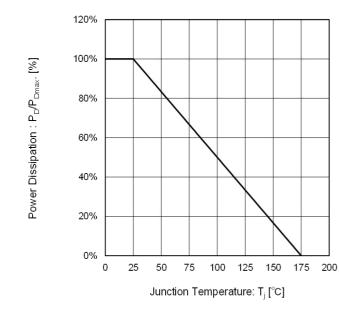
Deremeter	Sumbol	Symbol Conditions		Values			Lincit
Parameter	Зупрог			Min.	Тур.	Max.	Unit
Total acta charge	0		V <sub>GS</sub> = 10V	-	42.0	-	
Total gate charge	$Q_{g}$	V <sub>DD</sub> ≃ 20V		-	27.0	-	nC
Gate - Source charge	Q <sub>gs</sub>	I <sub>D</sub> = 10A	V <sub>GS</sub> = 6V	-	10.7	-	nc
Gate - Drain charge	$Q_{gd}$			-	8.0	-	

## •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Deremeter	Symbol Conditions		Values			Unit
Parameter			Min.	Тур.	Max.	Unit
Continuous forward current	I <sub>S</sub>	T <sub>a</sub> = 25℃	-	-	64	А
Pulse forward current	I <sub>SP</sub> *2	$T_{a} = 25 C$	-	-	160	А
Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 64A	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> = 10A, V <sub>GS</sub> =0V	-	49	-	ns
Reverse recovery charge	Q <sub>rr</sub>	di/dt = 100A/µs	-	49	-	nC



# •Electrical characteristic curves



# Fig.1 Power Dissipation Derating Curve

1000 Operation in this area is limited by R<sub>DS</sub>(on)(V<sub>GS</sub> = -10V) P<sub>W</sub> = 100µs 100 10 P<sub>₩</sub> = 1ms 1 0.1 T,=25℃ Single Pulse 0.01 0.01 0.1 1 10 100 Drain - Source Voltage : V<sub>DS</sub> [V]

Drain Current : I<sub>D</sub> [A]

## Fig.2 Maximum Safe Operating Area

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

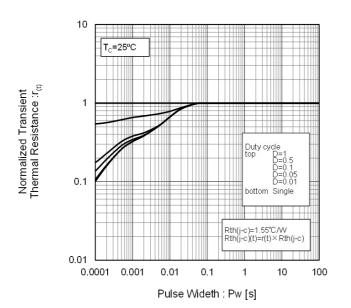
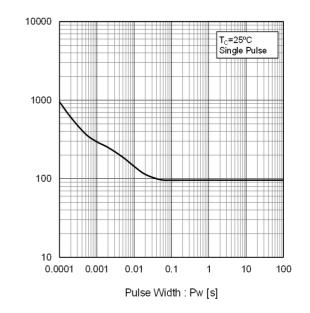


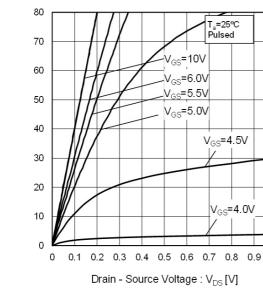
Fig.4 Single Pulse Maximum Power dissipation



Peak Transient Power : P[W]



#### • Electrical characteristic curves



Drain Current : I<sub>D</sub> [A]

### Fig.5 Typical Output Characteristics(I)

T₃=25ºC Pulsed

V<sub>GS</sub>=4.5V

V<sub>GS</sub>=4.0V

1

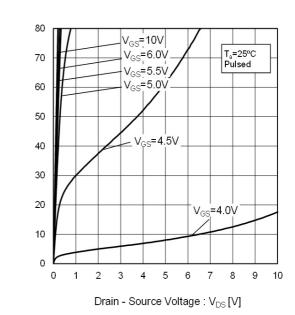
-V<sub>GS</sub>=10V

V<sub>GS</sub>=6.0V

V<sub>GS</sub>=5.5V

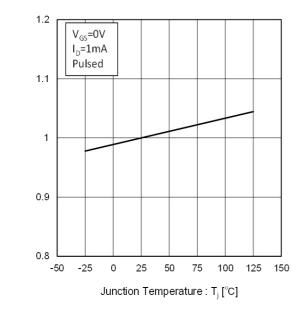
V<sub>GS</sub>=5.0V

Drain Current : I<sub>D</sub> [A]

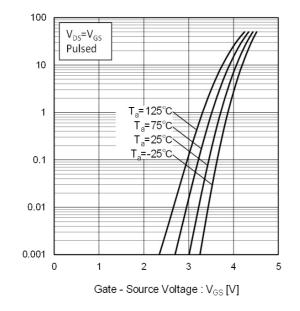


## Fig.6 Typical Output Characteristics(II)

Fig.7 Breakdown Voltage vs. **Junction Temperature** 

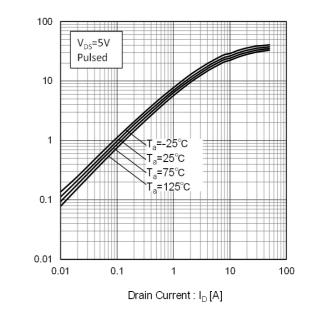






## Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature

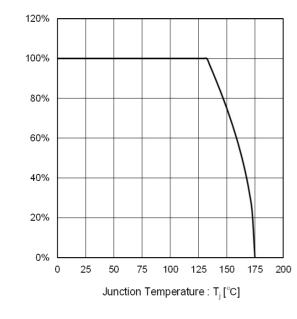


Forward Transfer Admittance :  $Y_{f_{5}}$  [S]

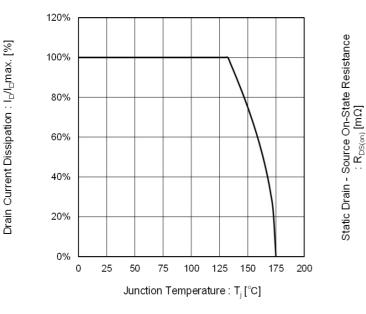
## Fig.10 Forward Transfer Admittance vs. Drain Current

Drain Current Dissipation :  $I_D/I_D$ max. [%]

Drain Current : I<sub>D</sub> [A]







# Fig.11 Drain Current Derating Curve

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

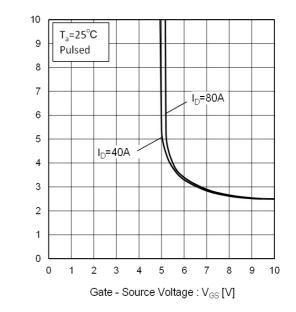
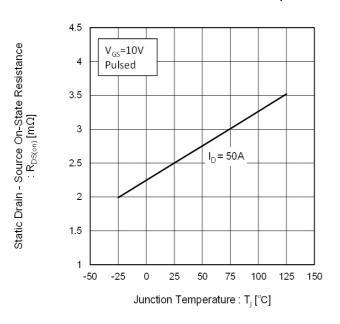


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





## • Electrical characteristic curves

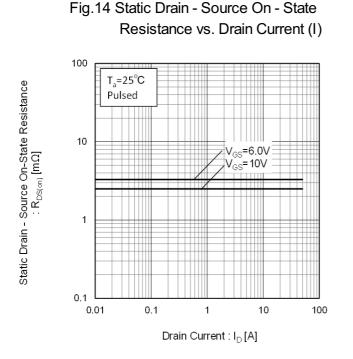


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

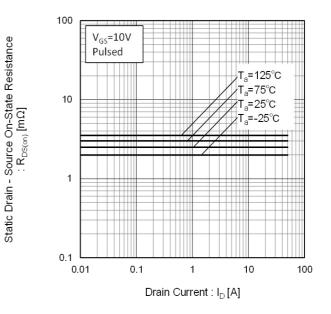
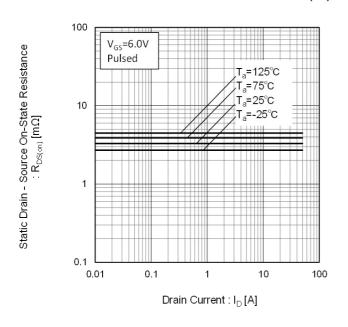
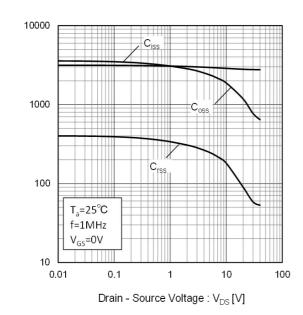


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)



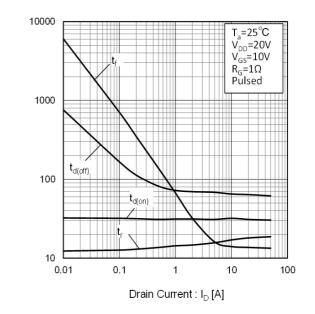


#### • Electrical characteristic curves



## Fig.17 Typical Capacitance vs. Drain - Source Voltage

Fig.18 Switching Characteristics



Switching Time : t [ns]

Source Current : I<sub>S</sub> [A]

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Fig.19 Dynamic Input Characteristics

Gate - Source Voltage : V<sub>GS</sub> [V]

Capacitance : C [pF]

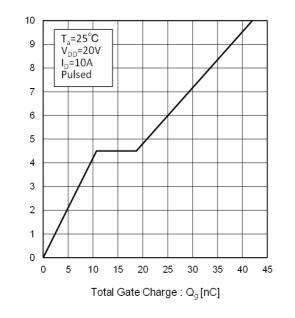
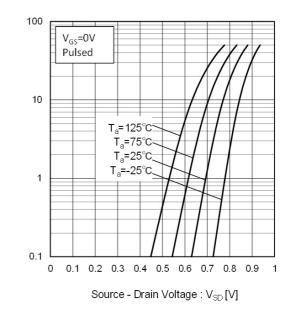


Fig.20 Source Current vs. Source Drain Voltage





## Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

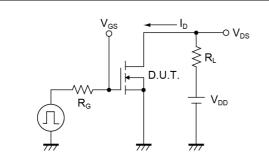


Fig.2-1 Gate Charge Measurement Circuit

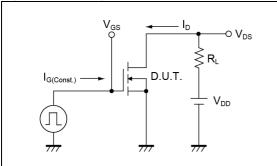


Fig.3-1 Avalanche Measurement Circuit

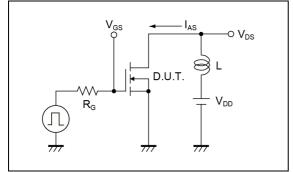


Fig.1-2 Switching Waveforms

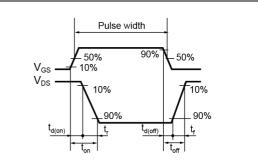
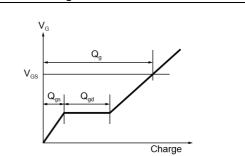
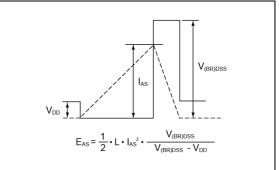


Fig.2-2 Gate Charge Waveform

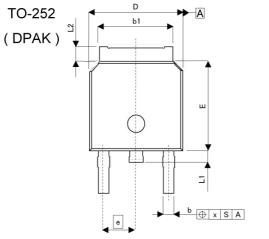


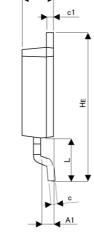
#### Fig.3-2 Avalanche Waveform

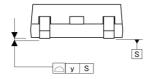


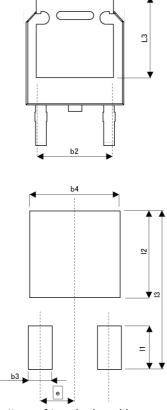


#### Dimensions









Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIME	TERS	INCI	HES
	MIN	MAX	MIN	MAX
A	2.10	2.30	0.083	0.091
A1	0.70	1.10	0.028	0.043
b	0.65	0.85	0.026	0.033
b1	5.10	5.40	0.201	0.213
b2	5.	10	0.2	.01
С	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.40	6.80	0.252	0.268
е	2.	2.30		91
E	6.00	6.40	0.236	0.252
HE	9.50	10.50	0.374	0.413
L	2.	90	0.1	14
L1	0.70	0.90	0.028	0.035
L2	0.70	1.30	0.028	0.051
L3	5.	30	0.2	.09
x	-	0.25	-	0.010
у	-	0.10	-	0.004

DIM MILIMETE		ETERS	INC	HES
	MIN	MAX	MIN	MAX
b3	-	1.10	-	0.043
b4		5.40	-	0.213
1	-	2.90	-	0.114
12	-	5.50	-	0.217
13	-	10.50	-	0.413

Dimension in mm/inches



# Notice

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 If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

JAPAN	USA	EU	CHINA
CLASSII	CLASSⅢ	CLASS II b	
CLASSⅣ	CLASSI	CLASSII	CLASSII

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  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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